

Application No. **09/839,941**

LED w/GaN substrate, AlGaInNPAs

7/15/02

East Search

Search	L.No.	Hits	Text Search			Data Bases
IS&R	L1	2802	(257/18,22,85,94,103,190,200,201).CCL S.		7/15/02 14:45	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L5	3	algainnasp algainasnp algainpasn gaalinnasp gaalinasnp gaalinpasn		7/15/02 15:26	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L8	53	1 and gan adj substrate		7/15/02 15:27	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L9	19	gaalinnasp gaalinasnp gaalinpasn inalgnasp inalgaasnp inalgapasn		7/15/02 15:18	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L10	11	9 and @ay<2000		7/15/02 15:27	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L11	2910	algainnasp algainasnp algainpasn gaalinnasp gaalinasnp gaalinpasn		7/15/02 15:26	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L12	64	11 and gan adj substrate		7/15/02 15:27	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L13	32	12 and @ay<2000		7/15/02 15:27	USPAT; EPO; JPO; Derwent; IBM TDB

Search Result

USPAT	Date	Page	Title	CI/Sub	CI/Sub	Inventor
US 20010048114 A1	20011206	10	SEMICONDUCTOR SUBSTRATE AND SEMICONDUCTOR DEVICE	257/103	257/627; 257/95; 372/43	MORITA, ETSUO et al.
US 6359292 B1	20020319	11	Semiconductor light emitting element	257/103	257/201; 257/613; 257/96	Sugawara, Hideto et al.
US 6339014 B1	20020115	9	Method for growing nitride compound semiconductor	438/503	257/103; 438/509	Ishida, Masahiro et al.
US 6191439 B1	20010220	10	Semiconductor light emitting device	257/103	257/95; 257/97	Sugawara, Hideto
US 5689123 A	19971118	21	III-V arsenide-nitride semiconductor materials and devices	257/190	257/18; 257/184; 257/201; 257/22	Major, Jo S. et al.
US 20010008656 A1	20010719	11	NITRIDE AND METHOD OF MAKING SAME	428/34.1	428/64.1	TISCHLER, MICHAEL A. et al.
US 6370176 B1	20020409	13	Gallium nitride group semiconductor laser device and optical pickup apparatus	372/45		Okumura, Toshiyuki
US 6121121 A	20000919	5	Method for manufacturing gallium nitride compound semiconductor	438/481	438/341; 438/479	Koide, Norikatsu
US 5811319 A	19980922	12	gallium nitride group compound semiconductors	438/46	204/192.35; 438/47; 438/604	Koike, Masayoshi et al.
US 5742628 A	19980421	12	with an improved GaN system double heterostructure	372/45	257/77	Fujii, Hiroaki
US 5679152 A	19971021	10	Method of making a single crystals Ga*N article	117/97	117/1; 117/90; 117/915; 438/507	Tischler, Michael A. et al.
US 5432808 A	19950711	16	Compound semiconductor light-emitting device	372/45	257/77; 372/44	Hatano, Ako et al.

L Number	Hits	Search Text	DB	Time stamp
1	2802	(257/18,22,85,94,103,190,200,201).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/15 14:45
5	3	algainnasp algainasnp algainpasn gaalinnasp gaalinasnp gaalinpasp inalganasp inalgaasnp inalgapasn alinganasp alingaasnp alingapasn gainalnbsp gainalasp gainalpasn ingaalnbsp ingaalasnp ingaalpasn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/15 14:53
8	53	((257/18,22,85,94,103,190,200,201).CCLS.) and gan adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/15 15:17
9	19	((257/18,22,85,94,103,190,200,201).CCLS.) and gan adj substrate) and (algainnasp algainasnp algainpasn gaalinnasp gaalinasnp gaalinpasp inalganasp inalgaasnp inalgapasn alinganasp alingaasnp alingapasn gainalnbsp gainalasp gainalpasn ingaalnbsp ingaalasnp ingaalpasn algainnas algainasp algainasp gaalinasnp gaalinasnp gaalinpasp inalganp inalganp inalgapn alinganasp alingaasnp alingapasn gainalnbsp gainalasp gainalpasn ingaalnbsp ingaalnp ingaalpn algainn gaalinn gainaln inalgan algainas gaalinas inalgaas algainp gaalinp inalgap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/15 15:18
10	11	((257/18,22,85,94,103,190,200,201).CCLS.) and gan adj substrate) and (algainnasp algainasnp algainpasn gaalinnasp gaalinasnp gaalinpasp inalganasp inalgaasnp inalgapasn alinganasp alingaasnp alingapasn gainalnbsp gainalasp gainalpasn ingaalnbsp ingaalasnp ingaalpasn algainnas algainasp algainasp gaalinasnp gaalinasnp gaalinpasp inalganp inalganp inalgapn alinganasp alingaasnp alingapasn gainalnbsp gainalasp gainalpasn ingaalnbsp ingaalnp ingaalpn algainn gaalinn gainaln inalgan algainas gaalinas inalgaas algainp gaalinp inalgap)) and @ay<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/15 15:18